AMENDMENTS TO THE SPECIFICATION

Please amend the specification as follows:

Please amend the paragraph at page 2, lines 9-19 as follows:

To achieve these and other advantages and in accordance with the purpose of the present invention, as embodied and broadly described, a nitride semiconductor includes: a substrate; a GaN-based buffer layer formed on the substrate in any one selected from a group consisting of a three-layered structure $\underline{Al_yIn_xGa_{1-(x+y)}N/In_xGa_{1-x}N/GaN}$ ~~$Al_yIn_xGa_{1-x,y}N/In_xGa_{1-x}N/GaN$~~ where $0 \leq x \leq 1$ and $0 \leq y \leq 1$, a two-layered structure $In_xGa_{1-x}N/GaN$ where $0 \leq x \leq 1$, and a superlattice structure of $In_xGa_{1-x}N/GaN$ where $0 \leq x \leq 1$; and a GaN-based single crystalline layer formed on the GaN-based buffer layer.

Please amend the paragraph at page 2, lines 20-29 as follows:

In an aspect of the present invention, there is provided a method for fabricating a nitride semiconductor. The method includes the steps of: (a) growing a GaN-based buffer layer on a substrate in any one selected from a group consisting of a three-layered structure $\underline{Al_yIn_xGa_{1-(x+y)}N/In_xGa_{1-x}N/GaN}$ ~~$Al_yIn_xGa_{1-x,y}N/In_xGa_{1-x}N/GaN$~~ where $0 \leq x \leq 1$ and $0 \leq y \leq 1$, a two-layered structure $In_xGa_{1-x}N/GaN$ where $0 \leq x \leq 1$, and a superlattice structure of

$In_xGa_{1-x}N$/GaN where $0 \leq x \leq 1$; and (b) growing a GaN-based single crystalline layer on the grown GaN-based buffer layer.

Please amend the paragraph starting at page 2, line 30 and ending at page 3, line 6 as follows:

In another aspect of the present invention, a nitride semiconductor light emitting device includes: a substrate; a GaN-based buffer layer formed on the substrate in any one selected from a group consisting of a three-layered structure $\underline{Al_yIn_xGa_{1-(x+y)}N/In_xGa_{1-x}N/GaN}$ ~~$Al_yIn_xGa_{1-x,y}N/In_xGa_{1-x}N/GaN$~~ where $0 \leq x \leq 1$ and $0 \leq y \leq 1$, a two-layered structure $In_xGa_{1-x}N$/GaN where $0 \leq x \leq 1$, and a superlattice structure of $In_xGa_{1-x}N$/GaN where $0 \leq x \leq 1$; a first electrode layer of an n-GaN layer formed on the GaN-based buffer layer; an activation layer formed on the first electrode layer; and a second electrode layer of a p-GaN layer formed on the activation layer.

Please amend the paragraph at page 4, lines 1-10 as follows:

The nitride semiconductor according to the present invention, as shown in FIG. 1(a), includes a substrate (i.e. a sapphire substrate or a SiC substrate) 101 and a GaN-based buffer layer 110 formed on the substrate 101 in three-layered structure $\underline{Al_yIn_xGa_{1-(x+y)}N/In_xGa_{1-x}N/GaN}$ ~~$Al_yIn_xGa_{1-x,y}N/In_xGa_{1-x}N/GaN$~~ 102 - 104 where $0 \leq x \leq 1$ and $0 \leq y \leq 1$. A GaN-based single crystalline layer 120 is formed on the GaN-based buffer layer 110. Here, the GaN-based single

crystalline layer 120 includes an Indium-doped GaN layer 105, an undoped GaN layer 106, and a silicon-doped n-GaN layer 107.

Please amend the paragraph at page 4, lines 18-26 as follows:

The GaN-based buffer layer 110 of the nitride semiconductor is grown in an MOCVD equipment at a temperature of 500 – 800 °C and in a thickness of 50 – 800 Å. The GaN-based buffer layer 110 is grown by while supplying carrier gases of H_2 and N_2, introducing sources of TMGa, TMIn and TMAl and gas of highly pure (>99.9995 %) NH_3 at the same time. Here, the flow of the sources of TMGa, TMIn and TMAl is 5 – 300 ~~μmol/mim~~ μmol/min, and the growing pressure is 100 – 700 torr.

Please amend the paragraph starting at page 7, line 31 and ending at page 8, line 2 as follows:

Here, the GaN-based buffer layer 402 is formed in any one selected from a group consisting of a three-layered structure $Al_yIn_xGa_{1-(x+y)}N/In_xGa_{1-x}N/GaN$ ~~$Al_yIn_xGa_{1-x,y}N/In_xGa_{1-x}N/GaN$~~ where $0 \leq x \leq 1$ and $0 \leq y \leq 1$, a two-layered structure $In_xGa_{1-x}N/GaN$ where $0 \leq x \leq 1$, and a superlattice structure of $In_xGa_{1-x}N/GaN$ where $0 \leq x \leq 1$.